

Gallium Arsenide Substrate

Product Specifications

N-Type, P-Type, Semi-insulating

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GaAs Wafers for LED Applications

Item	Specifications	Remarks
Conduction Type	SC/n-type	SC/p-type with Zn dope Available
Growth Method	VGF	
Dopant	Silicon	Zn available
Wafer Diamter	2, 3 & 4 inch	Ingot or as-cut availalbe
Crystal Orientation	(100)2°/6°/15° off (110)	Other misorientation available
OF	EJ or US	
Carrier Concentration	(0.4~2.5)E18/cm ³	
Resistivity at RT	(1.5~9)E-3 Ohm.cm	
Mobility	1500~3000cm ² /V.sec	
Etch Pit Density	<5000/cm ²	
Laser Marking	upon request	
Surface Finish	P/E or P/P	
Thickness	220~450um	
Epitaxy Ready	Yes	
Package	Single wafer container or cassette	



GaAs Wafers for LD Applications

Item	Specifications	Remarks
Conduction Type	SC/n-type	
Growth Method	VGF	
Dopant	Silicon	
Wafer Diameter	2, 3 & 4 inch	Ingot or as-cut available
Crystal Orientation	(100)2°/6°/15° off (110)	Other misorientation available
OF	EJ or US	
Carrier Concentration	(0.4~2.5)E18/cm ³	
Resistivity at RT	(1.5~9)E-3 Ohm.cm	
Mobility	1500~3000 cm ² /V.sec	
Etch Pit Density	<500/cm ²	
Laser Marking	upon request	
Surface Finish	P/E or P/P	
Thickness	220~350um	
Epitaxy Ready	Yes	
Package	Single wafer container or cassette	



GaAs Wafers, Semi-insulating for Microelectronics Applications

Item	Specifications	Remarks
Conduction Type	Insulating	
Growth Method	VGF	
Dopant	Undoped	
Wafer Diameter	2, 3, 4 & 6 inch	Ingot available
Crystal Orientation	(100)+/- 0.5°	
OF	EJ, US or notch	
Carrier Concentration	n/a	
Resistivity at RT	>1E7 Ohm.cm	
Mobility	>5000 cm ² /V.sec	
Etch Pit Density	<8000 /cm ²	
Laser Marking	upon request	
Surface Finish	P/P	
Thickness	350~675um	
Epitaxy Ready	Yes	
Package	Single wafer container or cassette	